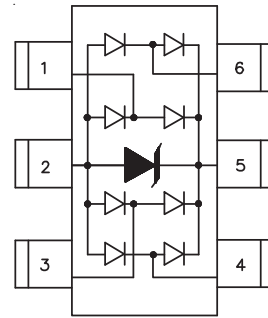
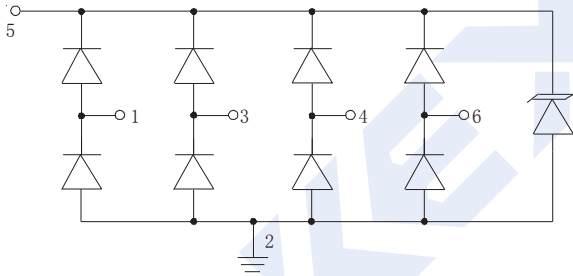
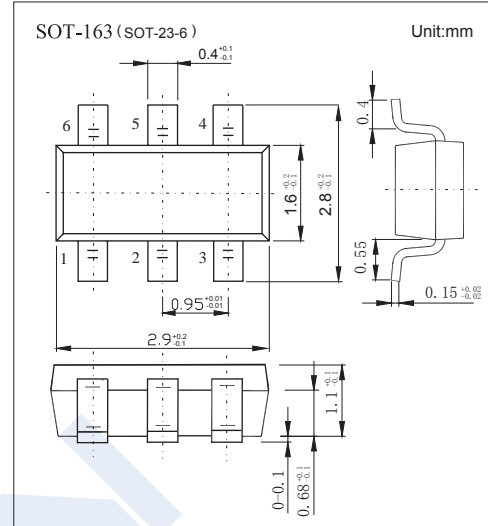


Low Capacitance TVS Diode Array

1KE05-6

■ Features

- ESD protection for high-speed data lines to IEC 61000-4-2 (ESD) $\pm 15\text{kV}$ (air), $\pm 8\text{kV}$ (contact)
- Protects four I/O lines
- Low capacitance: 0.5pF typical
- Low clamping voltage
- Low operating voltage: 5V

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
ESD per IEC 61000-4-2 (Air)	V _{ESD}	15	KV
ESD per IEC 61000-4-2 (Contact)		8	
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I _{PP}	5	A
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	P _{PP}	100	W
Lead Soldering Temperature	T _L	260 (10 Sec)	°C
Junction Temperature	T _J	125	
Storage Temperature range	T _{stg}	-55 to 150	

Low Capacitance TVS Diode Array

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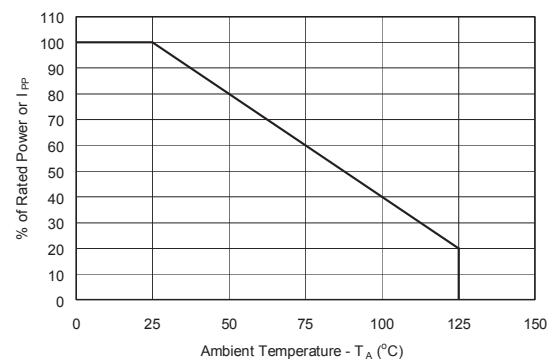
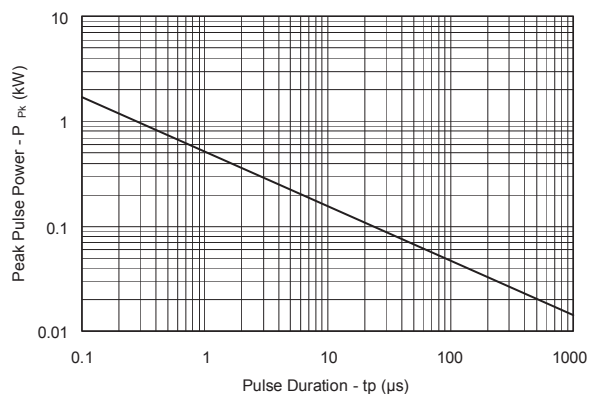
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Stand-Off Voltage	V_{RWM}	Pin 5 to 2			5	V
Reverse Breakdown Voltage	V_{BR}	$I_t = 1\text{ mA}$ Pin 5 to 2	6			
Forward voltage	V_F	$I_F = 15\text{ mA}$			1.2	
Clamping Voltage	V_C	$I_{PP} = 1\text{ A}$, $t_p = 8/20\mu\text{s}$ Any I/O pin to Ground			12	
		$I_{PP} = 5\text{ A}$, $t_p = 8/20\mu\text{s}$ Any I/O pin to Ground			16	
Reverse voltage leakage current	I_R	$V_{RWM} = 5\text{ V}$, $T = 25^\circ\text{C}$ Pin 5 to 2			1.0	μA
Junction Capacitance	C_J	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$ Any I/O pin to Ground		0.5	0.8	pF
		$V_R = 0\text{ V}$, $f = 1\text{ MHz}$ Between I/O pins		0.3	0.4	

■ Marking

Marking	V05
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■ Typical Characteristics



Low Capacitance TVS Diode Array

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Typical Characteristics

